Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3775	peltier and width	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 09:24
L2	66	peltier with width	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR ·	ON	2005/04/28 09:37
L3	1102	(peltier or thermoelectric or thermogenerator) with (width or length)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 09:38
L4	345	(peltier or thermoelectric or thermogenerator) with (width)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 09:38
S1	8	("thermo near 2 electric layer" or Peltier or thermo near2 generator) and "stress reduction"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 16:17
S2	8	("thermoelectric layer" or Peltier or thermo near2 generator) and "stress reduction"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 16:20
S3	7	"bottner, harald".in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 16:21
S4	27	"schubert, axel".in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 16:21

S5	6	"nurnus, joachim".in.	US-PGPUB;	OR	ON	2005/04/19 16:22
			USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB			
S6	1	"joegle, martin".in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 16:22
S7	31	S3 or S4 or S5 or S6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 16:26
S8	. 4	(("20020053359") or ("20030006470")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/19 16:28
S9	7	substrate and (thermo near2 electric near2 layer) and stress	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 16:30
S10	1126	substrate and ((thermo near2 electric near2 layer) or thermoelectric) and stress	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 16:30
S11	1125	substrate and (thermoelectric) and stress	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 16:31
S12	59	substrate and (thermoelectric near2 layer) and stress	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 16:37

S13	1	("19845104").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/19 16:38
S15	4	("10111185").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/19 16:39
S17	2	("6818470").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/20 09:26
S18	4	("3935610").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/20 09:28
S20	1016	substrate and stress and peltier	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/20 09:30
S21	7	substrate and (stress near2 reduction) and peltier	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2005/04/20 09:44
S22	182	(438/55).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/20 09:34
S23	2202	substrate and (stress near2 reduction)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/20 09:44

S26	324	(stress near2 reduction) and trench	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/20 10:06
S27	671	substrate and (antiadhesion or anti?adhesion)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/20 10:07
S28	179	substrate same (antiadhesion or anti?adhesion)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/20 10:13
S29	28	substrate and ((antiadhesion or anti?adhesion) near2 layer) and (ic or chip or semiconductor or "integrated circuit")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/20 10:22
S30	111	substrate and ((antiadhesion or anti?adhesion)) and (ic or chip or semiconductor or "integrated circuit")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/20 10:28
S31	50	substrate and ((antiadhesi\$3 or anti?adhesi\$3) near2 layer) and (ic or chip or semiconductor or "integrated circuit")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/20 10:41
S32	58	(cte or "coefficient of thermal expansion") and (peltier or thermo?electric or thermo?generator)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 12:56
S33	58	(cte or coefficient adj of adj thermal adj expansion) and (peltier or thermo?electric or thermo?generator)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 13:00

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S34	0	(titanium adj tungsten or tiw) and oxide and antiadhesion	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 13:02
S35	305	(titanium adj tungsten or tiw) and oxide and mems	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 15:24
S36	2131	(groove or trench) and (titantium near2 tungsten or tiw)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 13:23
S37	1	(groove or trench) and (titantium near2 tungsten or tiw) and (antiadhesi\$2 or anti-adhesi\$2)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2005/04/26 13:24
S38	508	(groove or trench) and (titantium near2 tungsten or tiw) and stress	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 13:25
S39	54	(groove or trench) and (titantium near2 tungsten or tiw) and stress near3 (reduction or reduced or reducting)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 13:30
S40	2	("6800933").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/26 13:37
S41	0	("peltiercooler").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/26 13:39

S43	109	"peltier cooler" and (groove or trench)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 13:40
S44	11	("5637921" "6082115" "6154366" "6173576" "6196002" "6281120" "6410840" "6429137" "6476483" "6485191" "6559538").PN. OR ("6800933"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/26 15:07
S45	1	("6410840").URPN.	USPAT	OR	ON	2005/04/26 14:23
S46	2	("6410840").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/26 15:08
S47	9	("1079445").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/26 15:08
S49	734	"peltier cooler"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 12:54
S50	5	"peltier cooler" and "thermoelectric layer"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 12:55
S51	1	("6410840").URPN.	USPAT	OR	ON	2005/04/27 12:59
S52	11	("5637921" "6082115" "6154366" "6173576" "6196002" "6281120" "6410840" "6429137" "6476483" "6485191" "6559538").PN. OR ("6800933"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/27 13:14
S53	0	"10131358".ap.	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/27 13:15
S54	6	"131358".ap.	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/27 13:15

S56	7	(cte or "thermal conductivity" or coefficient near2 thermal near2 conductivity) same ((sio2 or "silicon dioxide") and (bismuth telluride or bi2te3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 14:10
S57	3	(cte or "thermal conductivity" or coefficient near2 thermal near2 conductivity) same ((sio2 or "silicon dioxide") and ("bismuth telluride" or bi2te3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 14:11
S58	3	(cte or "thermal expansion" or coefficient near2 thermal near2 expansion) same ((sio2 or "silicon dioxide") and ("bismuth telluride" or bi2te3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 14:12
S59	27	(cte or "thermal expansion" or coefficient near2 thermal near2 expansion) same ("bismuth telluride" or bi2te3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 14:21
S60	27	(cte or "thermal expansion" or coefficient near2 thermal near2 expansion or "thermal expansion coefficient") same ("bismuth telluride" or bi2te3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 14:25
S61	157	(cte or "thermal expansion" or coefficient near2 thermal near2 expansion or "thermal expansion coefficient") same ("bismuth telluride" or bi2te3 or bite)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 14:25
S62	1	groove and "antiadhesion layer"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 15:23
S63	3	etch\$3 and "antiadhesion layer"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 15:23

S64	19600	(titanium adj tungsten or tiw) or (sio2 or "silicon dioxide") and mems and (groove or trench)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 15:26
S65	381	(titanium adj tungsten or tiw) and mems and (groove or trench)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2005/04/27 15:40
S66	833	(titanium adj tungsten or tiw) and "resist layer"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 15:40
S67	27	(titanium adj tungsten or tiw) with "resist layer"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 15:47
S68	347	(438/445).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/27 15:51
S70	69	S68 and "silicon dioxide"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 15:55
S71	2519	mask near2 ("silicon dioxide" or sio2)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 15:56
S72	566	mask adj ("silicon dioxide" or sio2)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 15:57

ļ	S73	896	("silicon dioxide" or sio2) adj mask	US-PGPUB;	OR	ON	2005/04/28 09:23
Ì			1	USPAT;			
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İ				EPO; JPO;			
				DERWENT;			
				IBM_TDB			